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[Vishay Semiconductor/Diodes Division](#)
[VS-80EBU02HF4](#)

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www.vishay.com

VS-80EBU02HF4

Vishay Semiconductors

Ultrafast Soft Recovery Diode, 80 A FRED Pt®



Cathode — Anode

PowerTab®

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- AEC-Q101 qualified
- PowerTab® package
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

PRODUCT SUMMARY	
Package	PowerTab®
$I_F(AV)$	80 A
V_R	200 V
V_F at I_F	1.10 V
t_{rr} (typ.)	See recovery table
T_J max.	175 °C
Diode variation	Single die

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_R			200	V
Continuous forward current	$I_F(AV)$	$T_C = 131$ °C	80	A	
Single pulse forward current	I_{FSM}	$T_C = 25$ °C	800		
Maximum repetitive forward current	I_{FRM}	Square wave, 20 kHz	160		
Operating junction and storage temperatures	T_J, T_{Stg}			-55 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_r	$I_R = 50$ µA	200	-	-	V
Forward voltage	V_F	$I_F = 80$ A	-	0.94	1.10	
		$I_F = 80$ A, $T_J = 175$ °C	-	0.77	0.88	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	50	µA
		$T_J = 150$ °C, $V_R = V_R$ rated	-	-	2	mA
Junction capacitance	C_T	$V_R = 200$ V	-	89	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	3.5	-	nH



DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$T_J = 25^\circ\text{C}$	$I_F = 80\text{ A}$ $V_R = 160\text{ V}$ $dI_F/dt = 200\text{ A}/\mu\text{s}$	-	40	-	ns
		$T_J = 125^\circ\text{C}$		-	75	-	
Peak recovery current	I_{RRM}	$T_J = 25^\circ\text{C}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	-	4.0	-	A
		$T_J = 125^\circ\text{C}$		-	8.8	-	
Reverse recovery charge	Q_{rr}	$T_J = 25^\circ\text{C}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	-	75	-	nC
		$T_J = 125^\circ\text{C}$		-	310	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R_{thJC}			-	-	0.5	°C/W
Thermal resistance, junction to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased		-	0.2	-	
Weight				-	-	5.02	g
				-	0.18	-	oz.
Mounting torque				1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab®		80EBU02H			

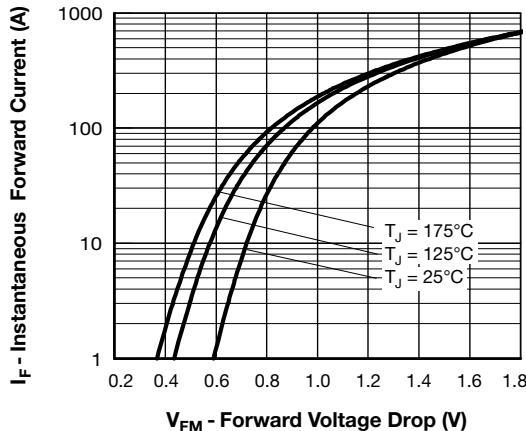


Fig. 1 - Maximum Forward Voltage Drop Characteristics

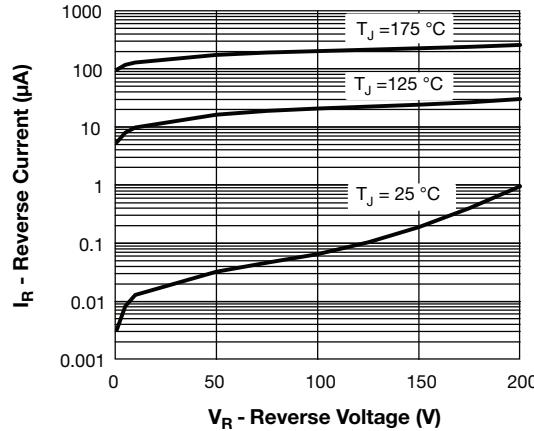


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

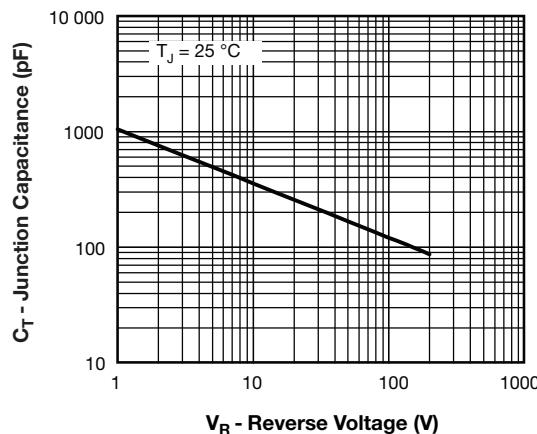


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

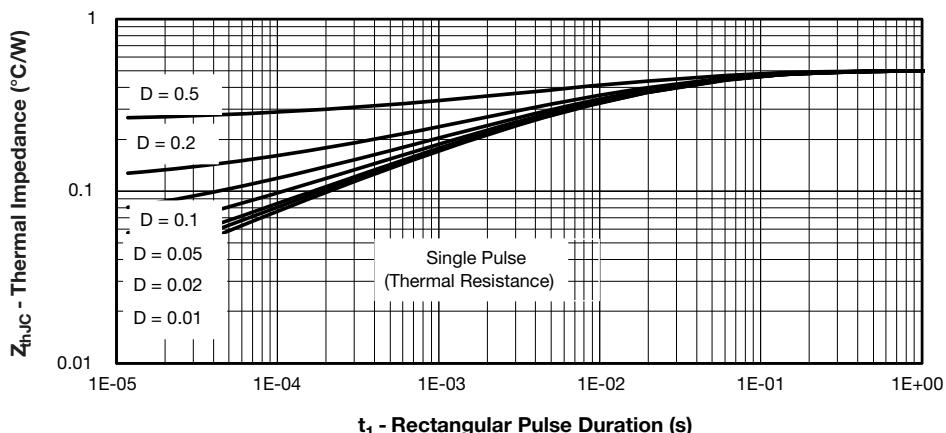


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

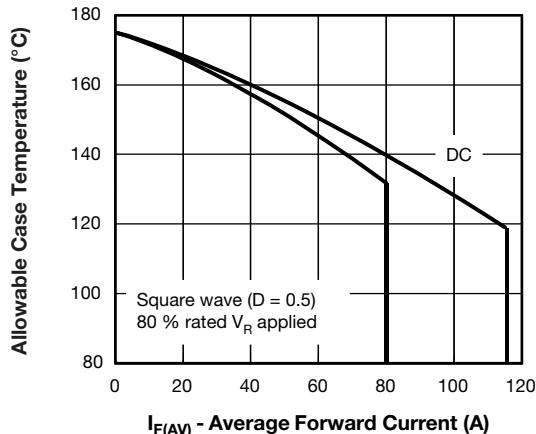


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

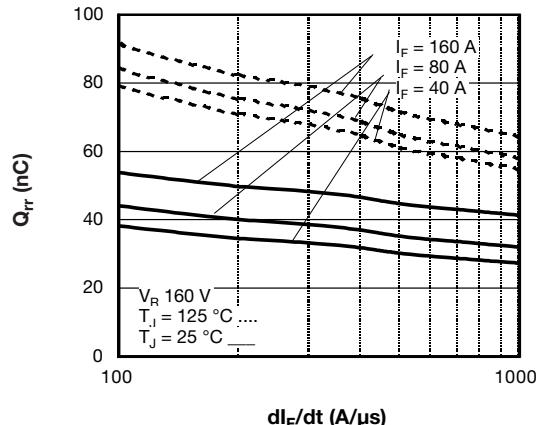


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

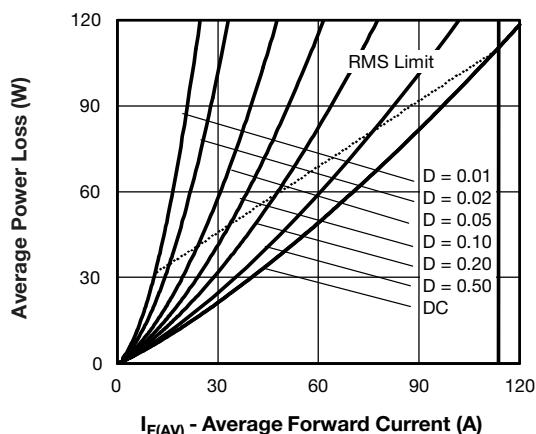


Fig. 6 - Forward Power Loss Characteristics

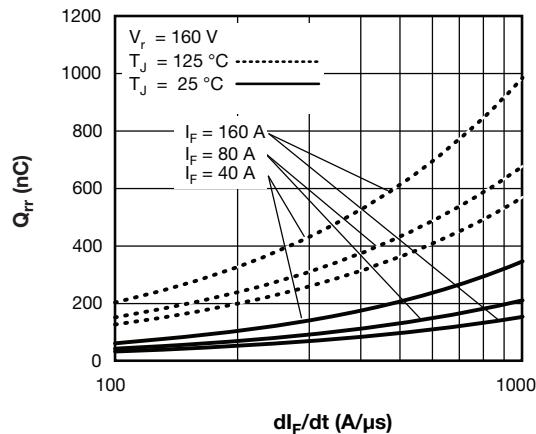
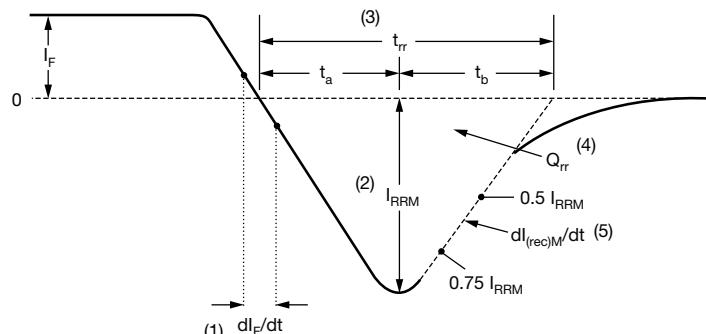


Fig. 8 - Typical Stored Charge vs. dI_F/dt



(1) dI_F/dt - rate of change of current through zero crossing

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

(2) I_{RRM} - peak reverse recovery current

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.5 I_{RRM}$ extrapolated to zero current.

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



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VS-80EBU02HF4

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	80	E	B	U	02	H	F4
	1	2	3	4	5	6	7	8
	1	- Vishay Semiconductors product						
	2	- Current rating (80 = 80 A)						
	3	- Single diode						
	4	- PowerTab®						
	5	- Ultrafast recovery						
	6	- Voltage rating (02 = 200 V)						
	7	- H = AEC-Q101 qualified						
	8	- Environmental digit: F4 = RoHS-compliant and totally lead (Pb)-free						

ORDERING INFORMATION (Example)

PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-80EBU02HF4	25	375	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS

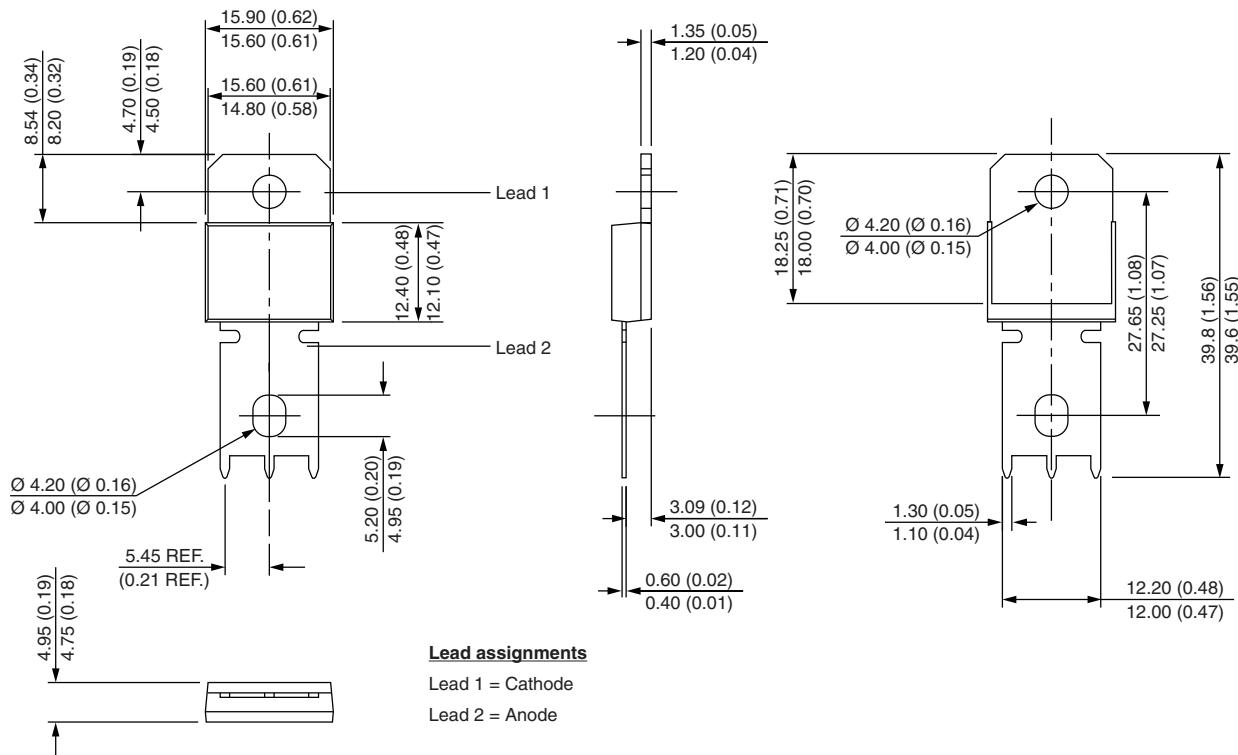
Dimensions	www.vishay.com/doc?95522
Part marking information	www.vishay.com/doc?95467
Application note	www.vishay.com/doc?95179

Outline Dimensions

Vishay Semiconductors

PowerTab®

DIMENSIONS in millimeters (inches)





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